

ABSTRACT OF THE DISCLOSURE

A semiconductor device, which is capable of improving isolation property of an isolation structure using STI without increasing impurity concentrations of wells, includes a well isolation structure in form of a shallow trench formed on the boundary between first and second wells opposite in conductivity type and adjacent to each other. When a first device region formed in the first well and a second device region formed in the second well are opposed at opposite sides of the well isolation structure, they are disposed at a first width (well isolation distance) than the second width when they are not opposed to each other. One of the device regions may be a dummy region which does not function as a circuit. In this configuration, angle of STI side walls is steeper, and STI width can be made smaller.